

Because each customer is unique and each business has its own specifities... TD next gives you the ability to integrate your own application

Through its flexibility, the TD1208 is the ideal

The high-end module for embedded applications!

Sigfox/LAN SDK GPS Integrated Antennas 25,40 12,7012,70

module to fit your core business needs!

into the TD1208 modules.

Product description

TD next's TD1208 devices are high performance, low current SIGFOX[™] gateways.

The combination of a powerful radio transceiver and a state-of-theart ARM Cortex M3 baseband processor achieves extremely high performance while maintaining ultra-low active and standby current consumption.

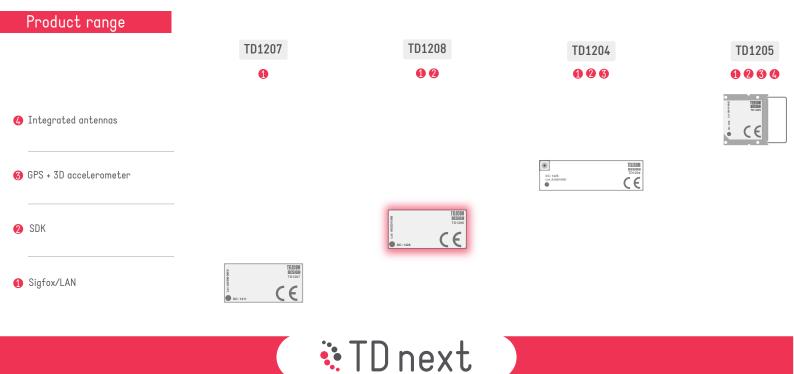
The TD1208 device offers an outstanding RF sensitivity of -126 dBm while providing an exceptional output power of up to +14 dBm with unmatched TX efficiency.

The TD1208 device versatility provides the gateway function from a local Narrow Band ISM network to the long-distance Ultra Narrow Band SIGFOX™ network at no additional cost.

The broad range of analog and digital interfaces available in the TD1208 module allows any application to interconnect easily to the SIGFOXTM network.

The LVTTL lowenergy UART, the I2C bus, the multiple timers with pulse count input/PWM output capabilities, the high-resolution/ high-speed ADC and DAC, along with the numerous GPIOs can control any kind of external sensors or activators.

Featuring an AES encryption engine and a DMA controller, the powerful 32- bit ARM Cortex-M3 baseband processor can implement highly complex and secure protocols in an efficient environmental and very low consumption way.



TD1208 Features

Sigfox certified Gateway & RF transceiver with antennas	Board characteristics
Frequency range = ISM 868 MHz Receive sensitivity = -126 dBm Modulation • (G)FSK, 4(G)FSK, GMSK • OOK Max output power • + 14 dBm Low active radio power consumption • 22 µA RX (windowed mode) • 37 mA TX @ +10 dBm	Power supply = 2.3 to 3.3 V LGA25 (25.4x12.7x3.81mm) Land Grid Array Package Available in several conditioning methods
	GND GND Reserved Reserved NC DB3 DB2 SDA SCL VDD USR0 USR1 U
Absolute maximum ratings	USR2 GND GND

Parameter	Value	Units
V _{DD} to GND	0 to +3.3	V
Instantaneous V $_{\rm RF-PEAK}$ to GND on RF Pin	-0.3 to +8.0	V
Sustained V $_{\rm \tiny RF-PEAK}$ to GND on RF Pin	-0.3 to +6.5	V
Voltage on Digital Inputs	0 to V _{DD}	V
Voltage on Analog Inputs	0 to V _{DD}	V
RX Input Power	+10	dBm
Operating Ambient Temperature Range T _A	-30 to +75	°C
Storage Temperature Range T _{STG}	-40 to +125	°C
Maximum soldeing Temperature	260	°C

DC power supply characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Supply Voltage Range	V _{DD}		2.3	3.0	3.3	V
Power Saving Mode	Sleep	Sleep current using the 32 kHz crystal @ 25°C	1.5	1.8	3.5	μA
Active CPU Mode	I _{Active}	CPU performing active loop @ 14 MHz	2.55	3.0	3.45	mA
Active CPU Mode + RX Mode Current	I _{RX}		-	13	16	mA
Active CPU Mode + TX Mode Current	I _{TX} +14	+14 dBm output power, 868 MHz, 3.3 V	-	49	-	mA
	I _{TX} +10	+10 dBm output power, 868 MHz, 3.3 V	-	37	-	mA

☑ contact@td-next.com

 +33 (0)5 57 35 63 70
 @ www.td-next.com



TD next ♀ Zone Actipolis - 22 bis rue Nully de Harcourt 33610 Canejan (FRANCE)